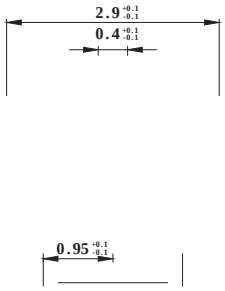
Features

ŏN-Channel Enhancement Mode Field Effect Transistor
ŏVDS=20V,RDS(ON)=40mΩ,VGS=4.5V,ID=5.0A
ŏVDS=20V,RDS(ON)=60mΩ,VGS=2.5V,ID=4.0A
ŏVDS=20V,RDS(ON)=75mΩ,VGS=1.8V,ID=1.0A

ŏMounting position:any



Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±10	V
Drain-Current -Continuous Tj=125 ℃	I_D	3.8	A
-Pulsed	I_{DM}	15	A
Power Dissipation *	P_D	1.25	W
Thermal Resistance,Junction- to-Ambient	R_{thJA}	100	℃/W
Operating Junction and Storage Temperature Range	Tj.Tstg	-55	℃

⩽